伯恩半导体
BORN SEMICONDUCTOR

MMST3906

PNP Plastic-Encapsulate Transistor

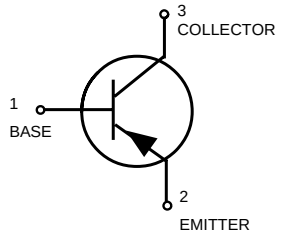
»Features

V_{CE} = -40V

I_C = -0.2A

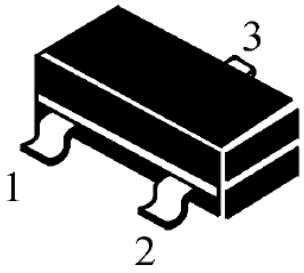
f_T =250MHZ @V_{CE}=-20V, I_C=-10mA,f=100MHz

»Pin Configurations



»General Description

- As complementary type the NPN transistor MMST3904 is recommended
- Epitaxial planar die constructio
- SOT-323 Plastic Package.



»Absolute Maximum Ratings @T_A=25℃ unless otherwise noted

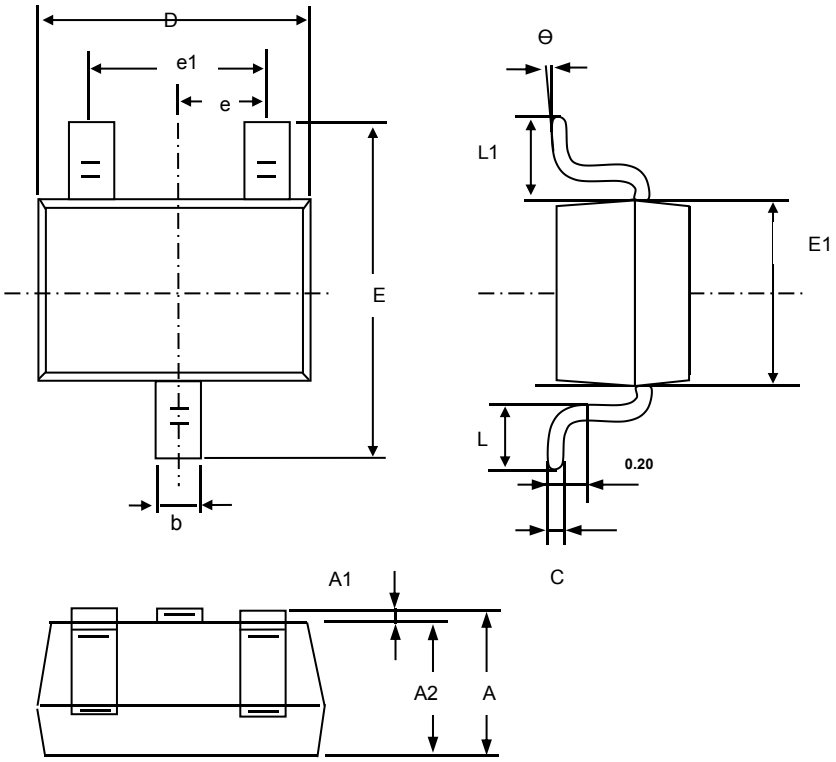
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-200	mA
P_{tot}	Total Device Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	625	℃/W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55 to +150	℃

»Electrical Characteristics @T_A=25℃ unless otherwise noted

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	I_C=-10μA, I_E=0	-50		V
Collector-emitter breakdown voltage	V_{CEO}	I_C=-1mA, I_B=0	-40		V
Emitter-base breakdown voltage	V_{EBO}	I_E=-10μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-40V, I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-10mA	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA, I_B= -5mA		-0.3	V
Transition frequency	f_T	V_{CE}=-20V, I_C=-10mA,f=100MHz	250		MHz
Delay Time	td	V_{CC}=-3V,V_{BE}=-0.5V		35	nS
Rise Time	tr	I_C=-10mA, I_{B1}=-I_{B2}=-1mA		35	nS
Storage Time	ts	V_{CC}=-3V,I_C=-10mA,		225	nS
Fall Time	tf	I_{B1}=-I_{B2}=-1mA		75	nS

»Package Information

SOT-323



Symbol	Dim in mm		
	Min	Nor	Max
A	0.90	1.00	1.10
A1	0.00	0.05	0.10
A2	0.90	0.95	1.00
b	0.20	0.30	0.40
c	0.08	0.12	0.15
D	2.00	2.10	2.20
E	2.15	2.30	2.45
E1	1.15	1.25	1.35
e	0.650TPY.		
e1	1.2	1.3	1.4
L	0.26	0.36	0.46
L1	0.525REF.		
θ	0°	4°	8°

»Ordering information

Order code	Package	Marking	Base qty	Delivery mode
MMST3906	SOT-323	K5N	3K	Tape and reel

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